

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 07-066119

(43)Date of publication of application : 10.03.1995

(51)Int.Cl.

H01L 21/027
G03F 7/42

(21)Application number : 05-232423

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(22)Date of filing : 25.08.1993

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(54) METHOD FOR REMOVING PHOTORESIST FILM

(57)Abstract:

PURPOSE: To allow quick removal of photoresist film through simple wet method without relying on the plasma ashing by subjecting the photoresist formed on the surface of a substrate to freezing prior to removal thereof.

CONSTITUTION: Liquid nitrogen is dripped, by a small quantity at a time, onto a photoresist film formed on the surface of a silicon wafer thus freezing and cracking the photoresist film. The silicon wafer is then immersed into methanol filling a cleaning tank and subjected to ultrasonic cleaning thus dissolving the photoresist film immediately into methanol. It is then washed with water thus obtaining a silicon wafer from which the photoresist film is removed. Alternatively, the photoresist film may be frozen by immersing the substrate into a refrigerant or bringing the photoresist film on the surface of substrate into contact with vapor of refrigerant, and the freezing time of 10sec-3min is normally sufficient.

LEGAL STATUS

[Date of request for examination] 24.08.2000

[Date of sending the examiner's decision of rejection] 28.06.2002

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's
decision of rejection]

[Date of requesting appeal against examiner's
decision of rejection]

[Date of extinction of right]

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